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(54) Title: METHOD OF MAKING A NANOSTRUCTURE

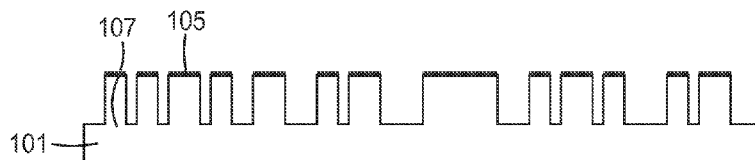


FIG. 1C

(57) Abstract: A method of making a nanostructure is provided that includes applying a thin, random discontinuous masking layer (105) to a major surface (103) of a substrate (101) by plasma chemical vapor deposition. The substrate (101) can be a polymer, an inorganic material, an alloy, or a solid solution. The masking layer (105) can include the reaction product of plasma chemical vapor deposition using a reactant gas comprising a compound selected from the group consisting of organosilicon compounds, metal alkyls, metal isopropoxides, metal acetylacetonates, and metal halides. Portions (107) of the substrate (101) not protected by the masking layer (105) are then etched away by reactive ion etching to make the nanostructures.

